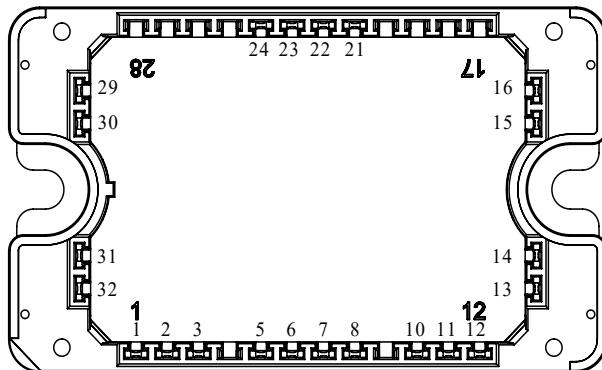
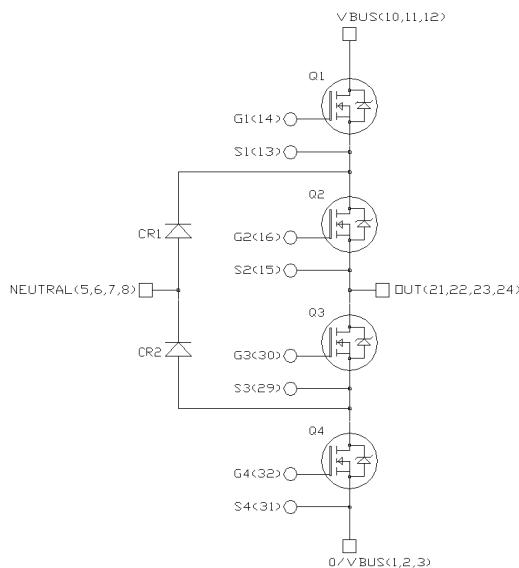


## Three Level Inverter SiC MOSFET Power Module

### Product Overview

The MSCSM120TLM50C3AG device is a 1200V/55A three level inverter silicon carbide (SiC) MOSFET power module.



**Note:**

1. All ratings at  $T_J = 25^\circ\text{C}$ , unless otherwise specified.
2. All multiple inputs and outputs must be shorted together: 1/2/3 ; 10/11/12 ; 5/6/7/8 ; 21/22/23/24



These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

## Features

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The following are the key features of MSCSM120TLM50C3AG device:

- SiC Power MOSFET
  - Low  $R_{DS(on)}$
  - High temperature performance
- SiC Schottky Diode (CR1 and CR2)
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature independent switching behavior
  - Positive temperature coefficient on VF
- Kelvin source for easy drive
- Low stray inductance
- High level of integration
- AlN substrate for improved thermal performance

## Benefits

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The following are the benefits of MSCSM120TLM50C3AG device:

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

## Application

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The following are the applications of MSCSM120TLM50C3AG device:

- Uninterruptible power supplies

## 1. Electrical Specifications

This section provides the electrical specifications of the MSCSM120TLM50C3AG device.

### 1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings of MSCSM120TLM50C3AG device.

**Table 1-1. Absolute Maximum Ratings**

Symbol	Parameter	Maximum Ratings		Unit
$V_{DSS}$	Drain-Source voltage	1200		V
$I_D$	Continuous drain current	$T_C = 25\text{ }^\circ\text{C}$	55	A
		$T_C = 80\text{ }^\circ\text{C}$	44	
$I_{DM}$	Pulsed drain current	110		
$V_{GSmax}$	Gate-Source voltage	-10/25		V
$R_{DS(on)}$	Drain-Source ON resistance	50		$\text{m}\Omega$
$P_D$	Power dissipation	$T_C = 25\text{ }^\circ\text{C}$	245	W

The following table lists the electrical characteristics of MSCSM120TLM50C3AG device.

**Table 1-2. Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{V}$ $V_{DS} = 1200\text{V}$		—	10	100	$\mu\text{A}$
$R_{DS(on)}$	Drain-Source on resistance	$V_{GS} = 20\text{V}$		$T_J = 25\text{ }^\circ\text{C}$	40	50	$\text{m}\Omega$
		$I_D = 40\text{A}$		$T_J = 175\text{ }^\circ\text{C}$	64	—	
$V_{GS(th)}$	Gate threshold voltage	$V_{GS} = V_{DS}$ $I_D = 1\text{ mA}$		1.8	2.7	—	V
$I_{GSS}$	Gate-Source leakage current	$V_{GS} = 20\text{V}$ $V_{DS} = 0\text{V}$		—	—	150	nA

The following table lists the dynamic characteristics of MSCSM120TLM50C3AG device.

**Table 1-3. Dynamic Characteristics**

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{GS} = 0V$ $V_{DS} = 1000V$ $f = 1\text{ MHz}$		—	1990	—	pF
$C_{oss}$	Output capacitance			—	156	—	
$C_{rss}$	Reverse transfer capacitance			—	17	—	
$Q_g$	Total gate charge	$V_{GS} = -5V/20V$ $V_{Bus} = 800V$ $I_D = 40A$		—	137	—	nC
$Q_{gs}$	Gate-Source charge			—	29	—	
$Q_{gd}$	Gate-Drain charge			—	31	—	
$T_{d(on)}$	Turn-on delay time	$V_{GS} = -5V/20V$ $V_{Bus} = 600V$ $I_D = 40A$	$T_J = 150\text{ }^{\circ}\text{C}$	—	30	—	ns
$T_r$	Rise time			—	40	—	
$T_{d(off)}$	Turn-off delay time			—	60	—	
$T_f$	Fall time			$R_{Gon} = 10\Omega$ $R_{Goff} = 5.8\Omega$		20	—
$E_{on}$	Turn-on energy	$V_{GS} = -5V/20V$ $V_{Bus} = 600V$ $I_D = 40A$	$T_J = 150\text{ }^{\circ}\text{C}$	—	0.8	—	mJ
$E_{off}$	Turn-off energy			—	0.53	—	
$R_{Gint}$	Internal gate resistance			—	1.2	—	Ω
$R_{thJC}$	Junction-to-case thermal resistance			—	—	0.61	°C/W

The following table lists the body diode ratings and characteristics of MSCSM120TLM50C3AG device.

**Table 1-4. Body Diode Ratings and Characteristics**

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
$V_{SD}$	Diode forward voltage	$V_{GS} = 0V$ $I_{SD} = 40A$		—	4	—	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 40A$		—	100	—	ns
$Q_{rr}$	Reverse recovery charge	$V_{GS} = -5V$		—	550	—	nC
$I_{rr}$	Reverse recovery current	$V_R = 800V$ $di_F/dt = 1000\text{ A}/\mu\text{s}$		—	13	—	A

## 1.2

**CR1 and CR2 SiC Diode Ratings and Characteristics (Per SiC Diode)**

The following table lists the CR1 and CR2 SiC diode ratings and characteristics (per SiC diode) of MSCSM120TLM50C3AG device.

**Table 1-5. CR1 and CR2 SiC Diode Ratings and Characteristics**

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
$V_{RRM}$	Peak repetitive reverse voltage			—	—	1200	V
$I_{RM}$	Reverse leakage current	$V_R = 1200$ V	$T_J = 25$ °C	—	10	200	μA
			$T_J = 175$ °C	—	150	—	
$I_F$	DC forward current		$T_C = 100$ °C	—	30	—	A
$V_F$	Diode forward voltage	$I_F = 30$ A	$T_J = 25$ °C	—	1.5	1.8	V
			$T_J = 175$ °C	—	2.1	—	
$Q_C$	Total capacitive charge	$V_R = 600$ V		—	130	—	nC
$C$	Total capacitance	$f = 1$ MHz $V_R = 400$ V		—	141	—	pF
		$f = 1$ MHz $V_R = 800$ V		—	105	—	
$R_{thJH}$	Junction-to-heat sink thermal resistance			—	—	0.9	°C/W

## 1.3

**Thermal and Package Characteristics**

The following table lists the thermal and package characteristics of the MSCSM120TLM50C3AG device.

**Table 1-6. Thermal and Package Characteristics**

Symbol	Characteristic			Min.	Max.	Unit
$V_{ISOL}$	RMS isolation voltage, any terminal to case $t = 1$ min, 50 Hz/60 Hz			4000	—	V
$T_J$	Operating junction temperature range			-40	175	°C
$T_{JOP}$	Recommended junction temperature under switching conditions			-40	$T_{Jmax}-25$	
$T_{STG}$	Storage case temperature			-40	125	
$T_c$	Operating case temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package weight			—	110	g

## 1.4

**Typical SiC MOSFET Performance Curve (Per SiC MOSFET)**

This section shows the typical SiC MOSFET performance curves of the MSCSM120TLM50C3AG device.

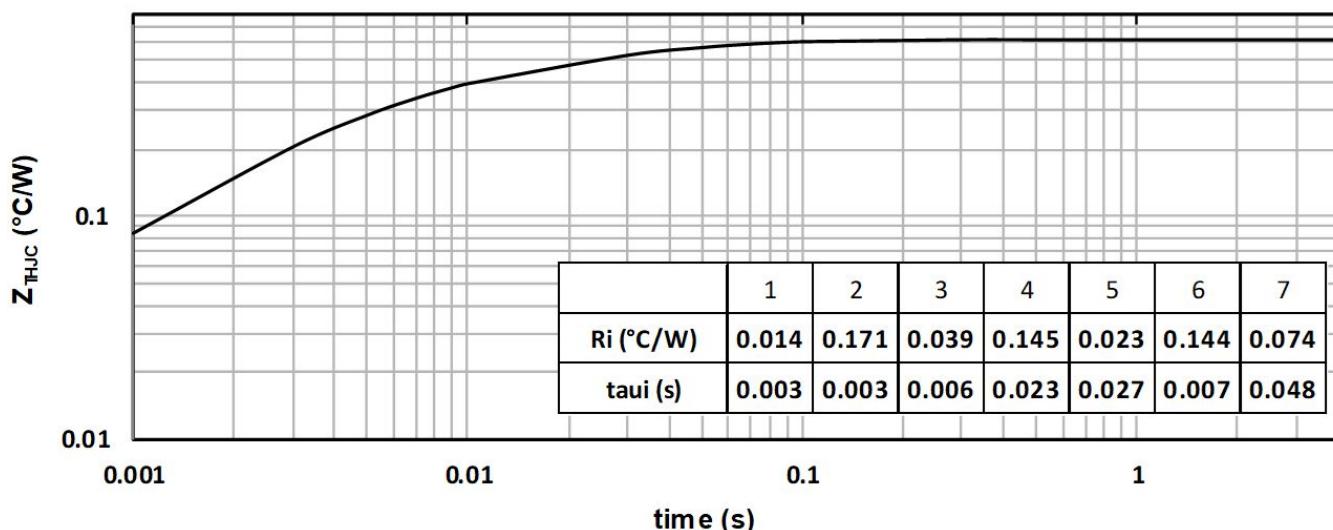
**Figure 1-1. Junction-to-Heatsink Thermal Impedance**

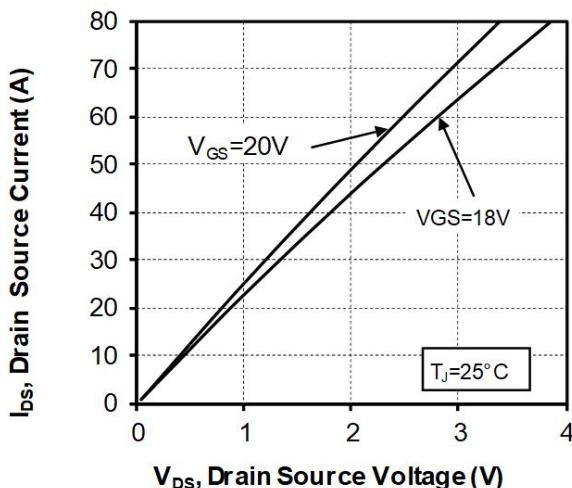
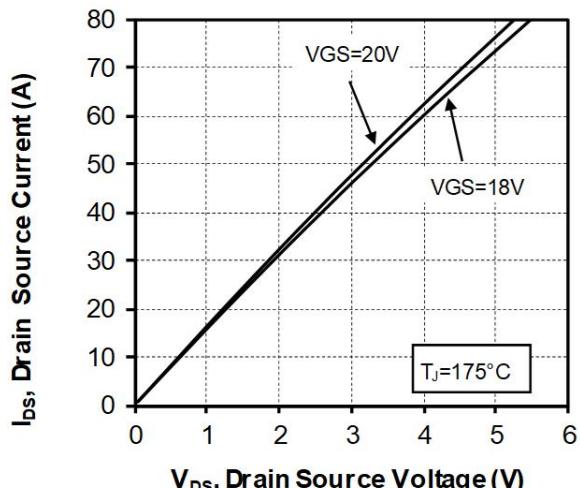
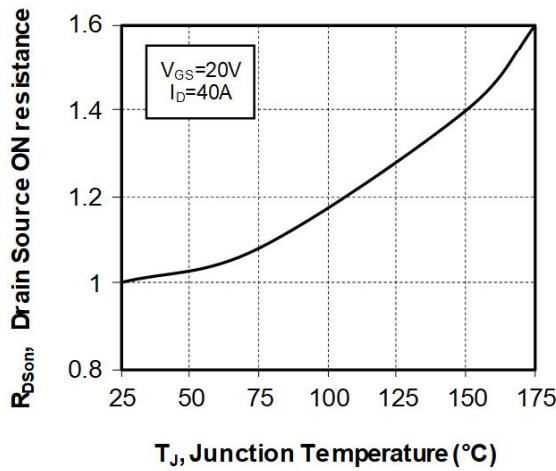
Figure 1-2. Output Characteristics,  $T_J = 25^\circ\text{C}$ Figure 1-3. Output Characteristics,  $T_J = 175^\circ\text{C}$ Figure 1-4. Normalized  $R_{DS(on)}$  vs. Temperature

Figure 1-5. Transfer Characteristics

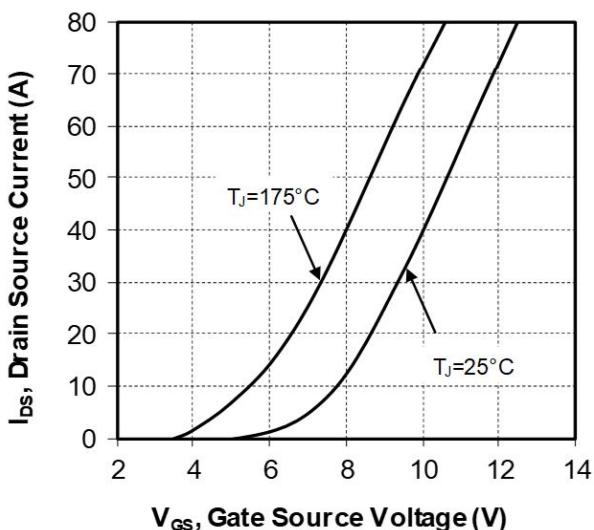
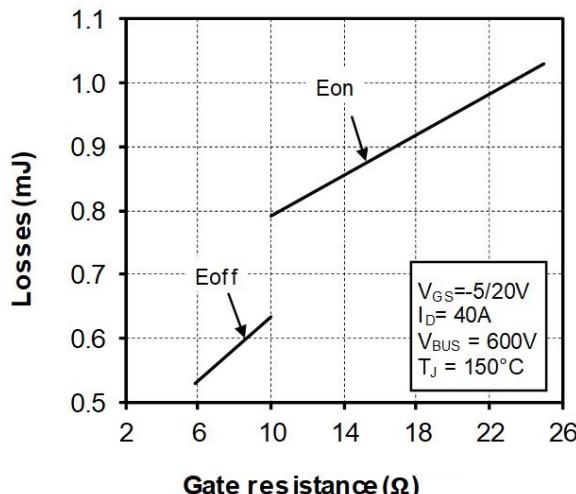
Figure 1-6. Switching Energy vs.  $R_g$ 

Figure 1-7. Switching Energy vs. Current

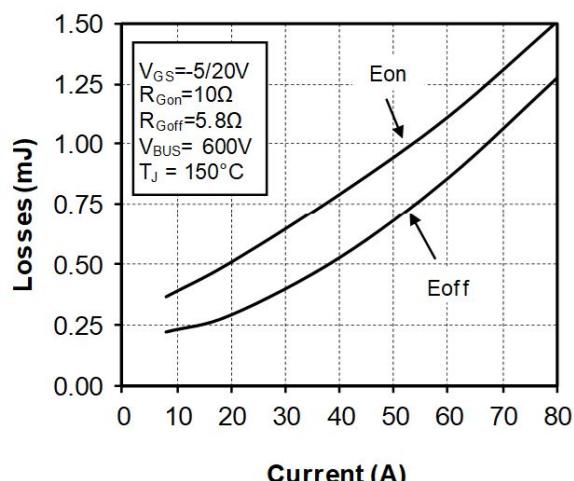


Figure 1-8. Capacitance vs. Drain Source Voltage

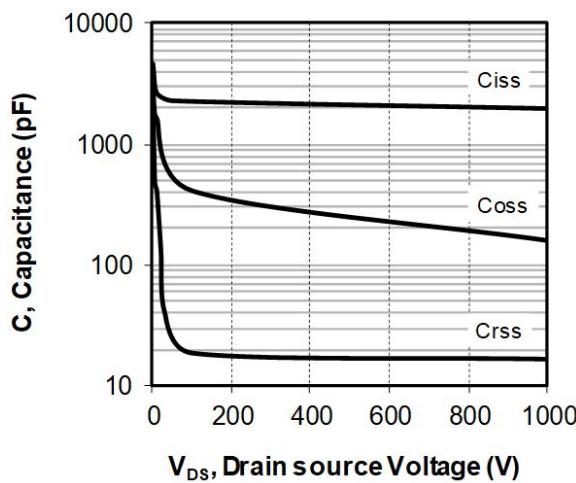


Figure 1-9. Gate Charge vs. Gate Source Voltage

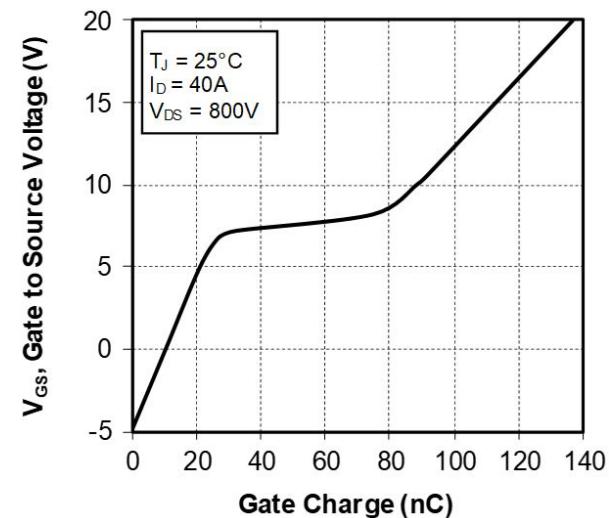
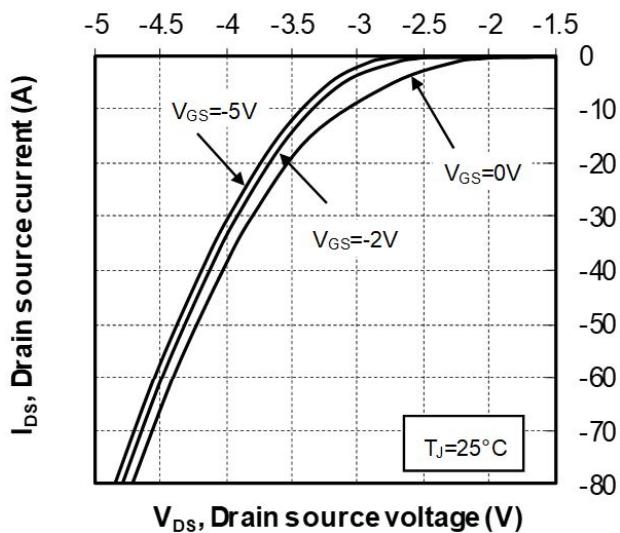
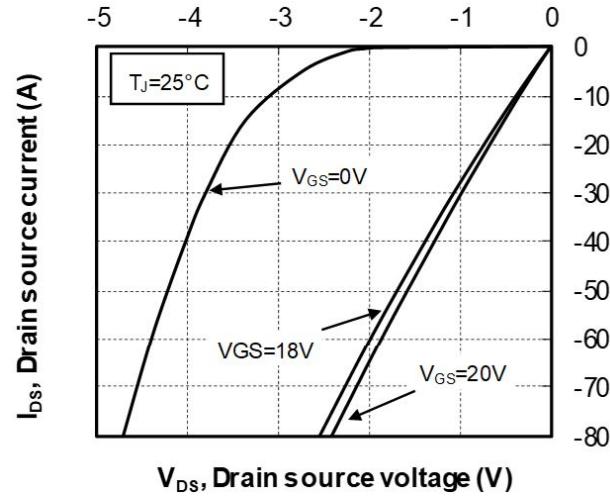
Figure 1-10. Body Diode Characteristics,  $T_J = 25^\circ\text{C}$ Figure 1-11. 3<sup>rd</sup> Quadrant Characteristics,  $T_J = 25^\circ\text{C}$ 

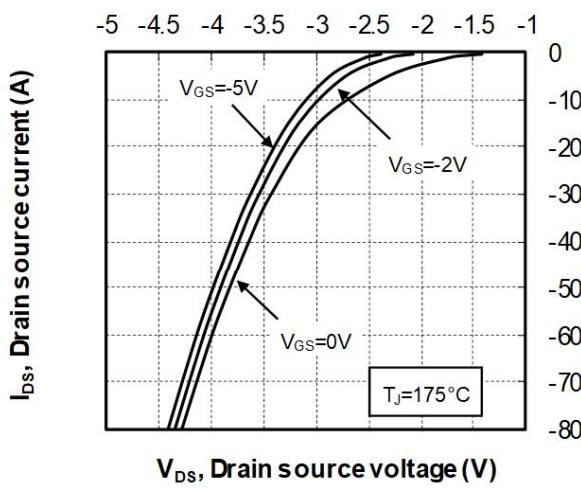
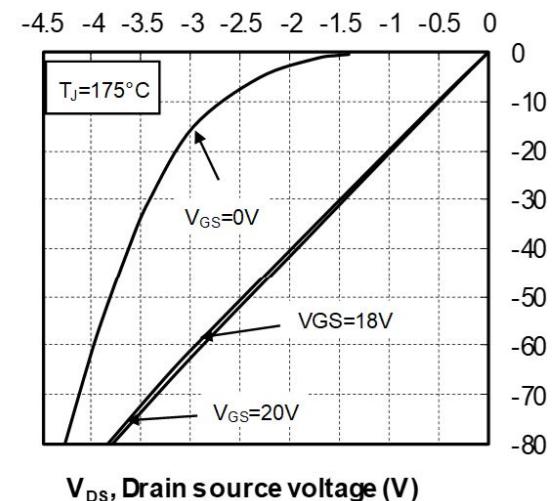
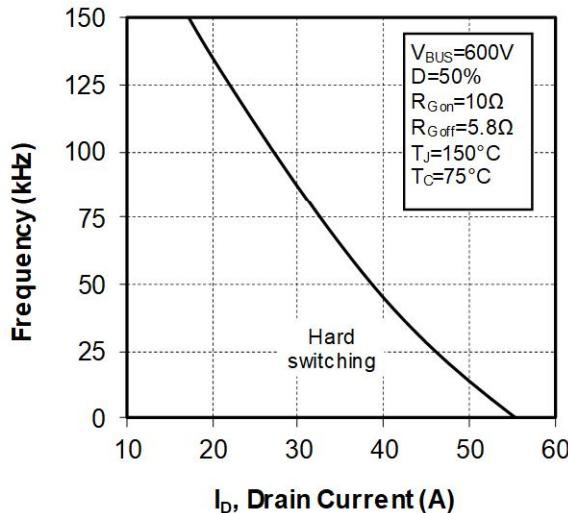
Figure 1-12. Body Diode Characteristics,  $T_J = 175^\circ\text{C}$ Figure 1-13. 3<sup>rd</sup> Quadrant Characteristics,  $T_J = 175^\circ\text{C}$ 

Figure 1-14. Operating Frequency vs. Drain Current



## 1.5

## Typical SiC Diode Performance Curves (Per SiC Diode)

This section shows the typical SiC diode performance curves of the MSCSM120TLM50C3AG device.

Figure 1-15. Junction-to-Heatsink Thermal Impedance

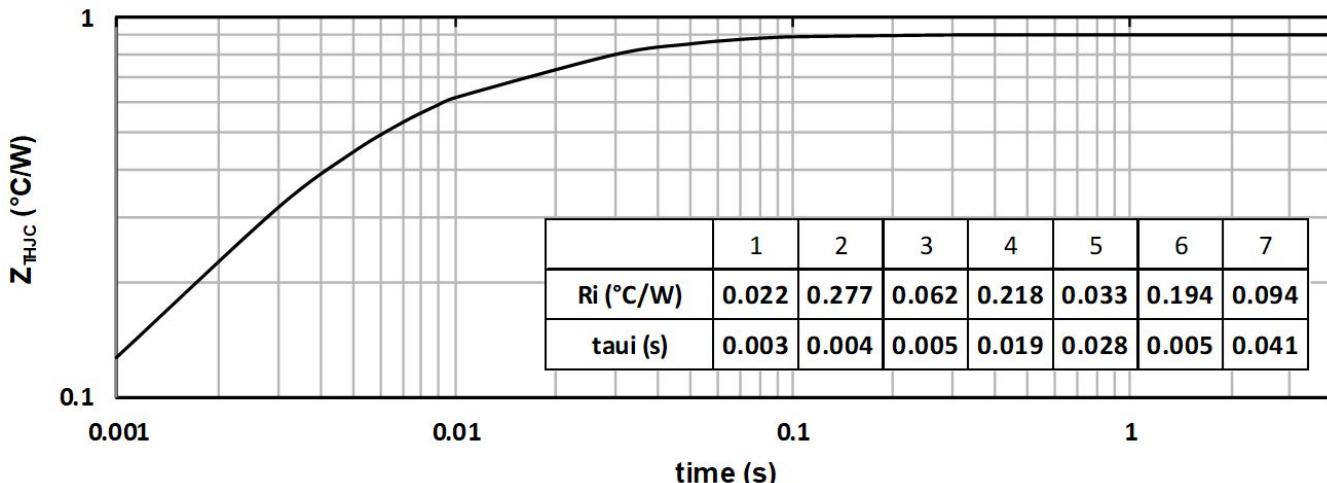


Figure 1-16. Forward Characteristics

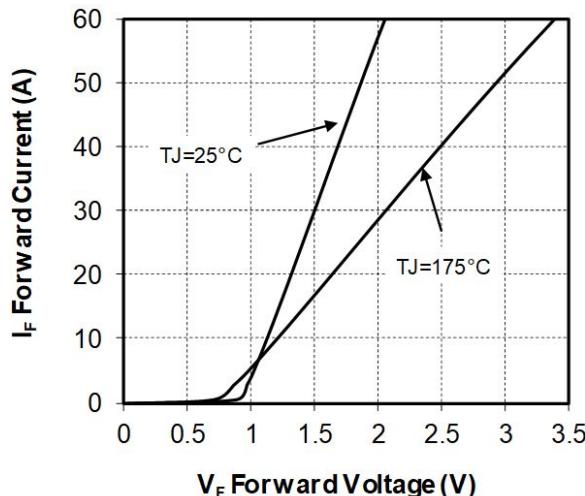
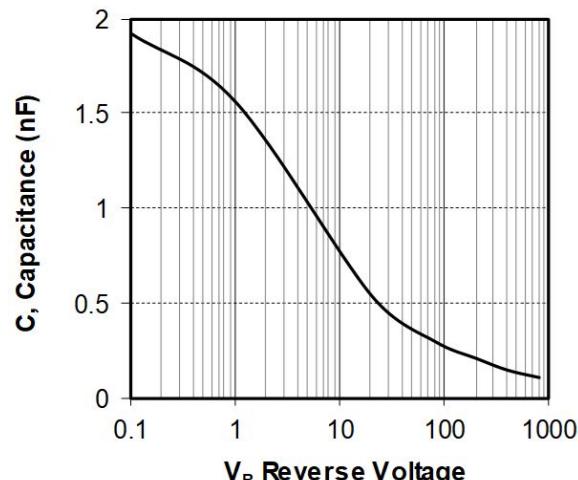


Figure 1-17. Capacitance vs. Reverse Voltage



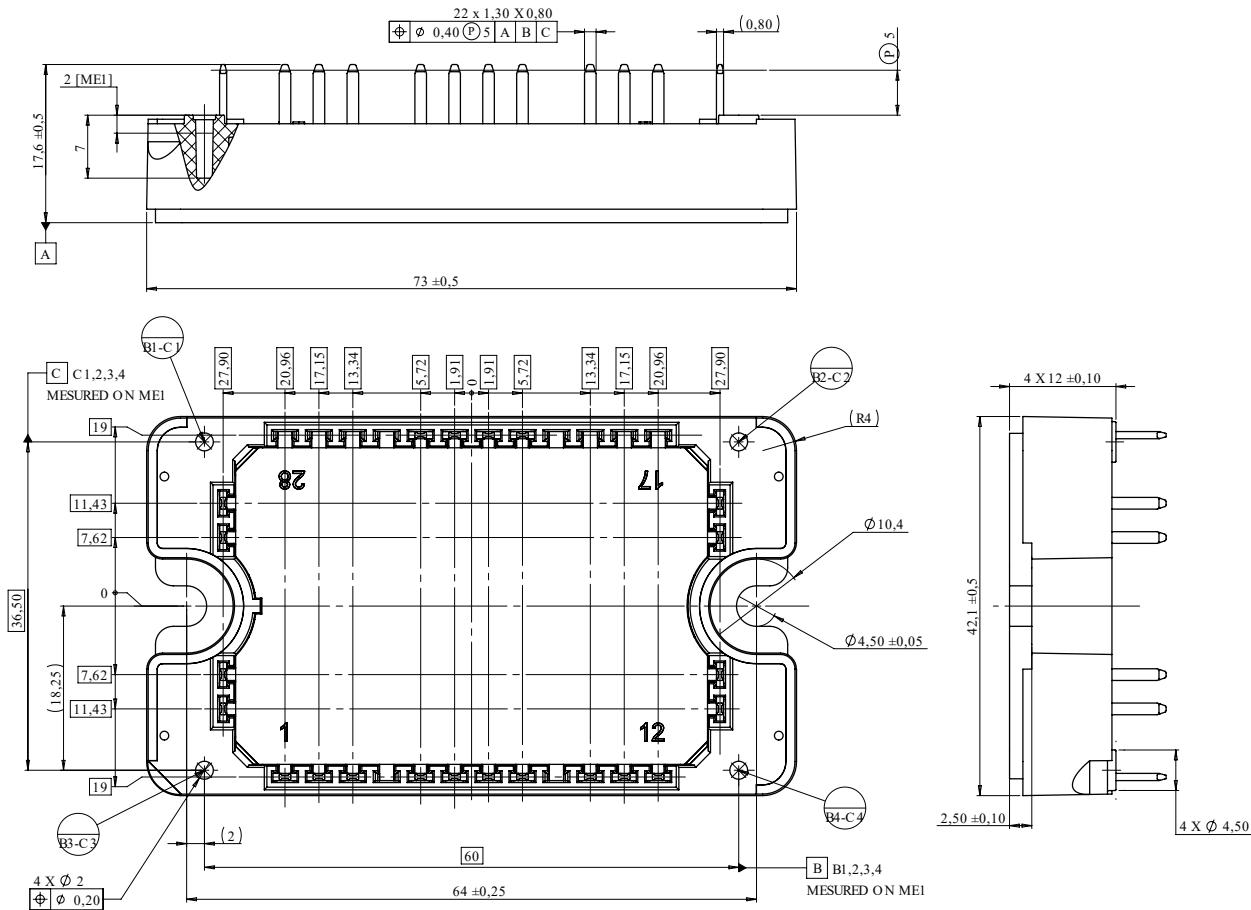
## 2. Package Specifications

The following section shows the package specification of the device.

### 2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM120TLM50C3AG device. The dimensions in the following figure are in millimeters.

**Figure 2-1. Package Outline Drawing**



**Note:** See application note [AN3500A—Mounting instructions for SP1F and SP3F power modules.](#)

### 3. Revision History

Revision	Date	Description
A	12/2021	Initial Revision

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